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# Zener Diodes, 24 and 40 Watt Peak Power

## SOT-23 Dual Common Anode Zeners

### MMBZxxxALT1G Series, SZMMBZxxxALT1G Series

These dual monolithic silicon Zener diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common anode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

#### Features

- SOT-23 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Standard Zener Breakdown Voltage Range – 5.6 V to 47 V
- Peak Power – 24 or 40 W @ 1.0 ms (Unidirectional), per Figure 6 Waveform
- ESD Rating:
  - Class 3B (> 16 kV) per the Human Body Model
  - Class C (> 400 V) per the Machine Model
- ESD Rating of IEC61000-4-2 Level 4, ±30 kV Contact Discharge
- Maximum Clamping Voltage @ Peak Pulse Current
- Low Leakage < 5.0 µA
- Flammability Rating UL 94 V-0
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

#### Mechanical Characteristics

**CASE:** Void-free, transfer-molded, thermosetting plastic case

**FINISH:** Corrosion resistant finish, easily solderable

**MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:**

260°C for 10 Seconds

Package designed for optimal automated board assembly

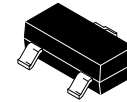
Small package size for high density applications

Available in 8 mm Tape and Reel

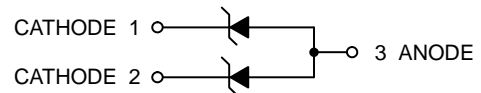
Use the Device Number to order the 7 inch/3,000 unit reel.

Replace the “T1” with “T3” in the Device Number to order the

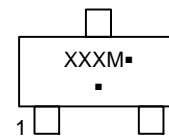
13 inch/10,000 unit reel.



SOT-23  
CASE 318  
STYLE 12



#### MARKING DIAGRAM



XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

#### DEVICE MARKING INFORMATION

See specific marking information in the device marking column of the table on page 3 of this data sheet.

## MMBZxxxALT1G Series, SZMMBZxxxALT1G Series

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation @ 1.0 ms (Note 1) MMBZ5V6ALT1G thru MMBZ9V1ALT1G @ $T_L \leq 25^\circ\text{C}$ MMBZ12VALT1G thru MMBZ47VALT1G	$P_{pk}$	24 40	W
Total Power Dissipation on FR-5 Board (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Power Dissipation on Alumina Substrate (Note 3) @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to +150	$^\circ\text{C}$
Lead Solder Temperature – Maximum (10 Second Duration)	$T_L$	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Non-repetitive current pulse per Figure 6 and derate above  $T_A = 25^\circ\text{C}$  per Figure 7.

2. FR-5 =  $1.0 \times 0.75 \times 0.62$  in.

3. Alumina =  $0.4 \times 0.3 \times 0.024$  in, 99.5% alumina.

\*Other voltages may be available upon request.

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MMBZ5V6ALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZMMBZ5V6ALT1G*	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBZ5V6ALT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBZ6VxALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZMMBZ6VxALT1G*	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBZ6VxALT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBZ9V1ALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBZ9V1ALT13G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBZxxVALT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZMMBZxxVALT1G*	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBZxxVALT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SZMMBZxxVALT3G*	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SZMMBZxxVALT1G*	SOT-23 (Pb-Free)	3,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

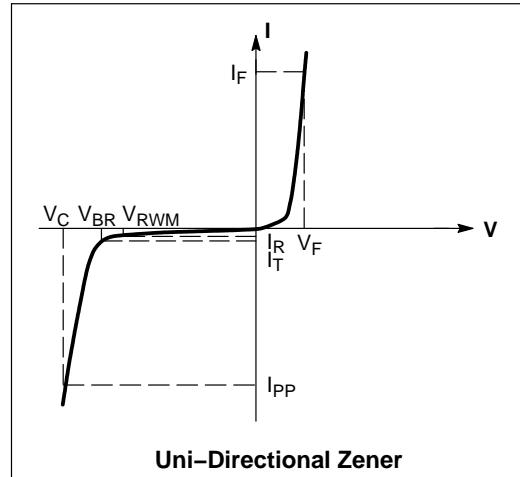
# MMBZxxxALT1G Series, SZMMBZxxxALT1G Series

## ELECTRICAL CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise noted)

**UNIDIRECTIONAL** (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>
V <sub>RWM</sub>	Working Peak Reverse Voltage
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>
V <sub>BR</sub>	Breakdown Voltage @ I <sub>T</sub>
I <sub>T</sub>	Test Current
ΘV <sub>BR</sub>	Maximum Temperature Coefficient of V <sub>BR</sub>
I <sub>F</sub>	Forward Current
V <sub>F</sub>	Forward Voltage @ I <sub>F</sub>
Z <sub>ZT</sub>	Maximum Zener Impedance @ I <sub>ZT</sub>
I <sub>ZK</sub>	Reverse Current
Z <sub>ZK</sub>	Maximum Zener Impedance @ I <sub>ZK</sub>



**ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

**UNIDIRECTIONAL** (Circuit tied to Pins 1 and 3 or Pins 2 and 3)

(V<sub>F</sub> = 0.9 V Max @ I<sub>F</sub> = 10 mA) (5% Tolerance)

**24 WATTS**

Device*	Device Marking	V <sub>RWM</sub> Volts	I <sub>R</sub> @ V <sub>RWM</sub> μA	Breakdown Voltage				Max Zener Impedance (Note 5)			V <sub>C</sub> @ I <sub>PP</sub> (Note 6)		ΘV <sub>BR</sub> mV/°C
				V <sub>BR</sub> (Note 4) (V)			@ I <sub>T</sub>	Z <sub>ZT</sub> @ I <sub>ZT</sub>	Z <sub>ZK</sub> @ I <sub>ZK</sub>		V <sub>C</sub>	I <sub>PP</sub>	
				Min	Nom	Max	mA	Ω	Ω	mA	V	A	
MMBZ5V6ALT1G/T3G	5A6	3.0	5.0	5.32	5.6	5.88	20	11	1600	0.25	8.0	3.0	1.26
MMBZ6V2ALT1G	6A2	3.0	0.5	5.89	6.2	6.51	1.0	—	—	—	8.7	2.76	2.80
MMBZ6V8ALT1G	6A8	4.5	0.5	6.46	6.8	7.14	1.0	—	—	—	9.6	2.5	3.4
MMBZ9V1ALT1G	9A1	6.0	0.3	8.65	9.1	9.56	1.0	—	—	—	14	1.7	7.5

(V<sub>F</sub> = 0.9 V Max @ I<sub>F</sub> = 10 mA) (5% Tolerance)

**40 WATTS**

Device*	Device Marking	V <sub>RWM</sub> Volts	I <sub>R</sub> @ V <sub>RWM</sub> nA	Breakdown Voltage				V <sub>C</sub> @ I <sub>PP</sub> (Note 6)		ΘV <sub>BR</sub> mV/°C
				V <sub>BR</sub> (Note 4) (V)			@ I <sub>T</sub>	V <sub>C</sub>	I <sub>PP</sub>	
				Min	Nom	Max	mA	V	A	
MMBZ12VALT1G	12A	8.5	200	11.40	12	12.60	1.0	17	2.35	7.5
MMBZ15VALT1G	15A	12	50	14.25	15	15.75	1.0	21	1.9	12.3
MMBZ16VALT1G	16A	13	50	15.20	16	16.80	1.0	23	1.7	13.8
MMBZ18VALT1G	18A	14.5	50	17.10	18	18.90	1.0	25	1.6	15.3
MMBZ20VALT1G	20A	17	50	19.00	20	21.00	1.0	28	1.4	17.2
MMBZ27VALT1G/T3G	27A	22	50	25.65	27	28.35	1.0	40	1.0	24.3
MMBZ33VALT1G	33A	26	50	31.35	33	34.65	1.0	46	0.87	30.4
MMBZ47VALT1G	47A	38	50	44.65	47	49.35	1.0	54	0.74	43.1

(V<sub>F</sub> = 0.9 V Max @ I<sub>F</sub> = 10 mA) (2% Tolerance)

**40 WATTS**

Device*	Device Marking	V <sub>RWM</sub> Volts	I <sub>R</sub> @ V <sub>RWM</sub> nA	Breakdown Voltage				V <sub>C</sub> @ I <sub>PP</sub> (Note 6)		ΘV <sub>BR</sub> mV/°C
				V <sub>BR</sub> (Note 4) (V)			@ I <sub>T</sub>	V <sub>C</sub>	I <sub>PP</sub>	
				Min	Nom	Max	mA	V	A	
MMBZ16VTALT1G	16T	13	50	15.68	16	16.32	1.0	23	1.7	13.8
MMBZ47VTALT1G	47T	38	50	46.06	47	47.94	1.0	54	0.74	43.1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. V<sub>BR</sub> measured at pulse test current I<sub>T</sub> at an ambient temperature of 25°C.

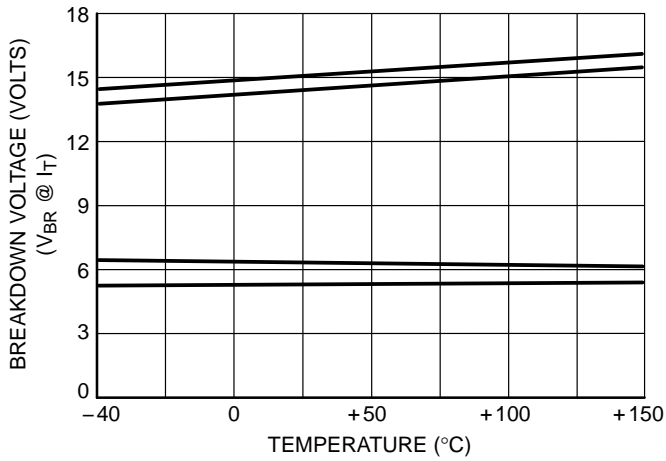
5. Z<sub>ZT</sub> and Z<sub>ZK</sub> are measured by dividing the AC voltage drop across the device by the AC current applied. The specified limits are for I<sub>Z(AC)</sub> = 0.1 I<sub>Z(DC)</sub>, with the AC frequency = 1.0 kHz.

6. Surge current waveform per Figure 6 and derate per Figure 7

\* Include SZ-prefix devices where applicable.

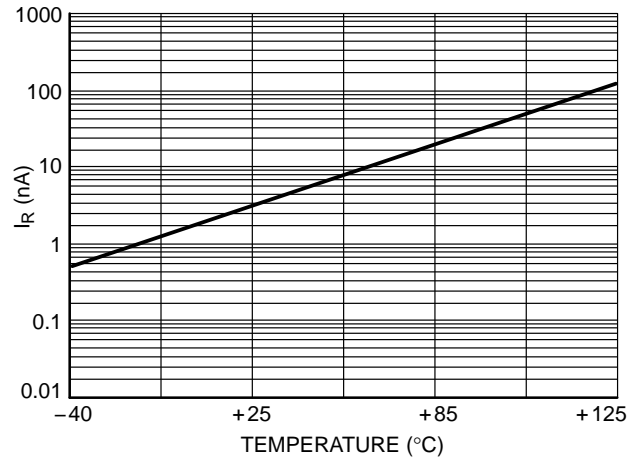
# MMBZxxxALT1G Series, SZMMBZxxxALT1G Series

## TYPICAL CHARACTERISTICS

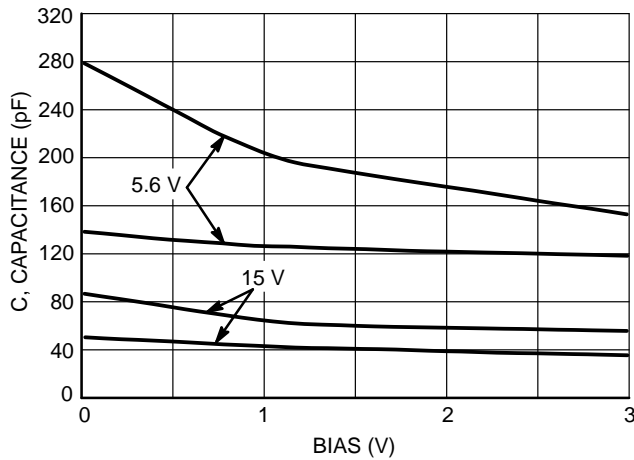


**Figure 1. Typical Breakdown Voltage versus Temperature**

(Upper curve for each voltage is bidirectional mode, lower curve is unidirectional mode)

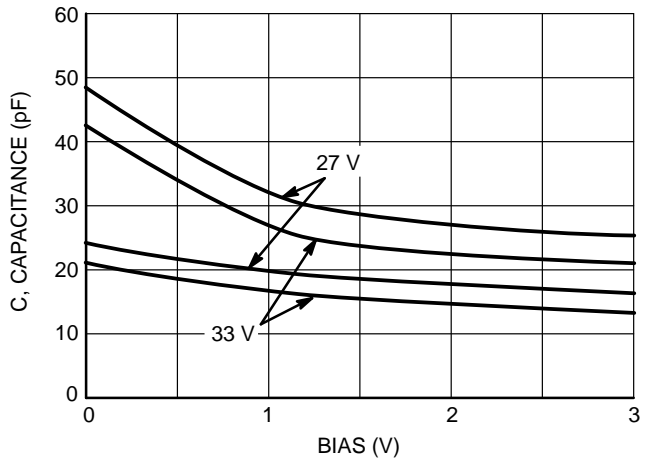


**Figure 2. Typical Leakage Current versus Temperature**



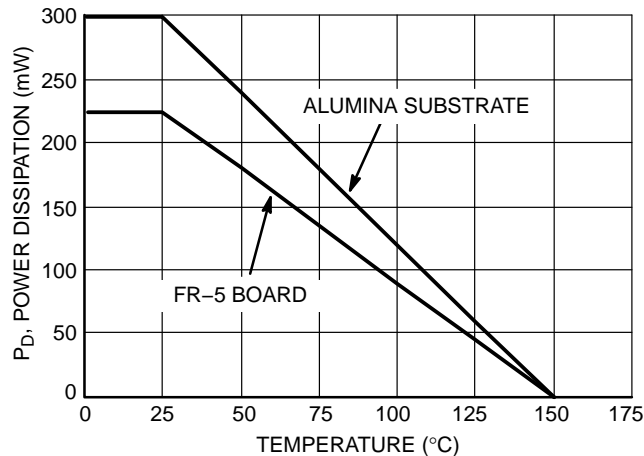
**Figure 3. Typical Capacitance versus Bias Voltage**

(Upper curve for each voltage is unidirectional mode, lower curve is bidirectional mode)



**Figure 4. Typical Capacitance versus Bias Voltage**

(Upper curve for each voltage is unidirectional mode, lower curve is bidirectional mode)



**Figure 5. Steady State Power Derating Curve**

## TYPICAL CHARACTERISTICS

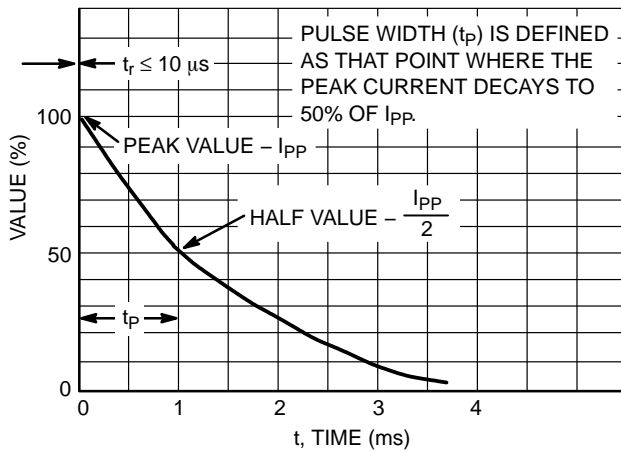


Figure 6. Pulse Waveform

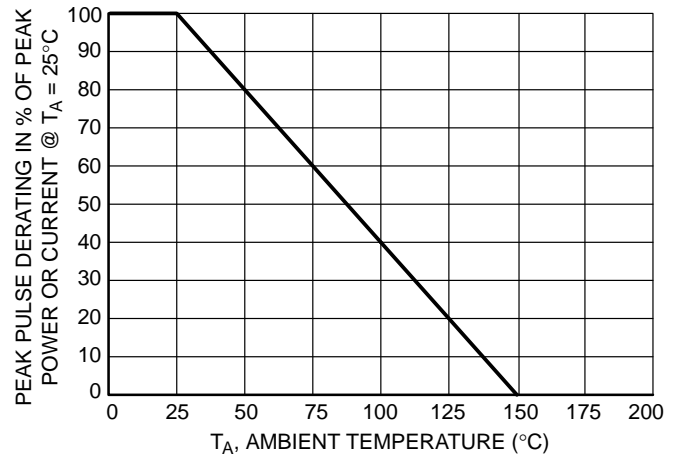


Figure 7. Pulse Derating Curve

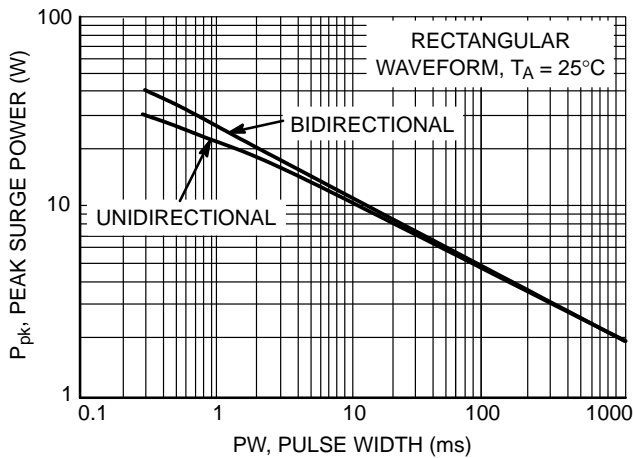


Figure 8. Maximum Non-repetitive Surge Power,  $P_{pk}$  versus PW

Power is defined as  $V_{RSM} \times I_Z(pk)$  where  $V_{RSM}$  is the clamping voltage at  $I_Z(pk)$ .

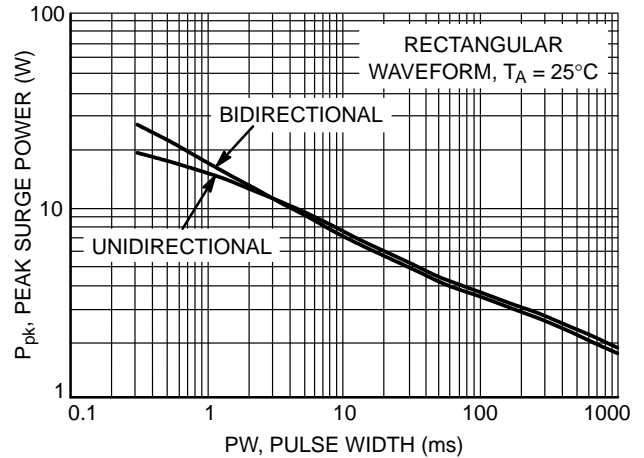


Figure 9. Maximum Non-repetitive Surge Power,  $P_{pk(NOM)}$  versus PW

Power is defined as  $V_Z(NOM) \times I_Z(pk)$  where  $V_Z(NOM)$  is the nominal Zener voltage measured at the low test current used for voltage classification.

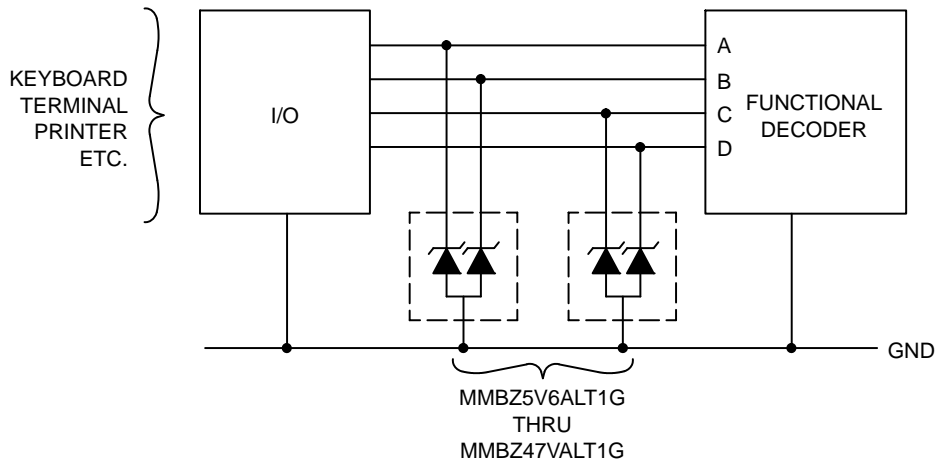
## MMBZxxxALT1G Series, SZMMBZxxxALT1G Series

### TYPICAL COMMON ANODE APPLICATIONS

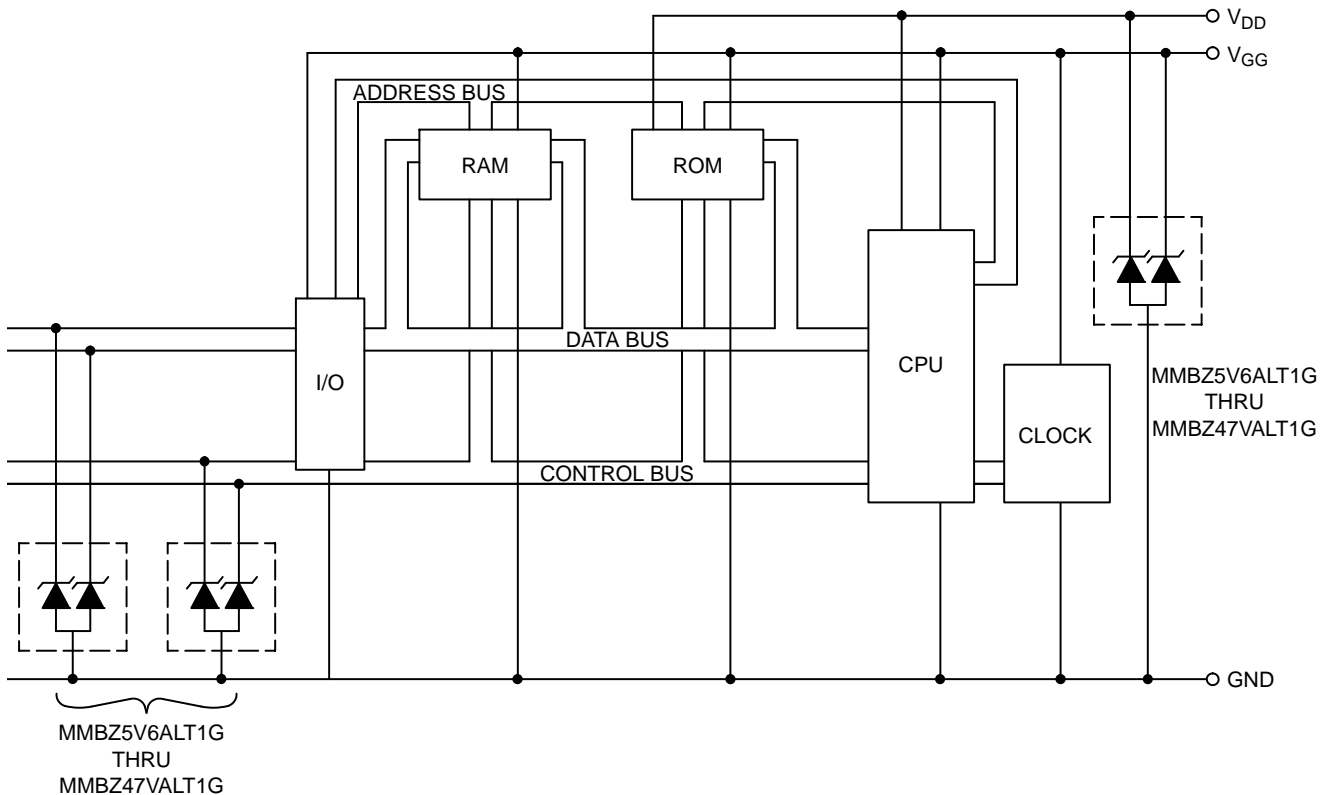
A dual junction common anode design in a SOT-23 package protects two separate lines using only one package. This adds flexibility and creativity to PCB design especially

when board space is at a premium. Two simplified examples of ESD applications are illustrated below.

#### Computer Interface Protection



#### Microprocessor Protection

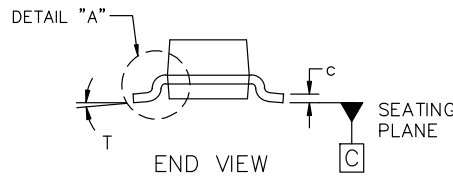
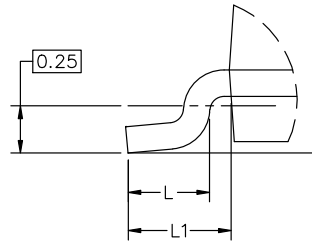




SCALE 4:1

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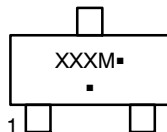


MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC  
MARKING DIAGRAM\*



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



\* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

STYLES ON PAGE 2

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**CASE 318**  
**ISSUE AU**

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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